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 Approved by: H. Yamaguchi 21-Sep.-2010

MITSUBISHI HVDi MODULES
RM250DG-130F

HIGH POWER SWITCHING USE
 INSULATED TYPE

HVDi (High Voltage Diode) Modules

RM250DG-130F



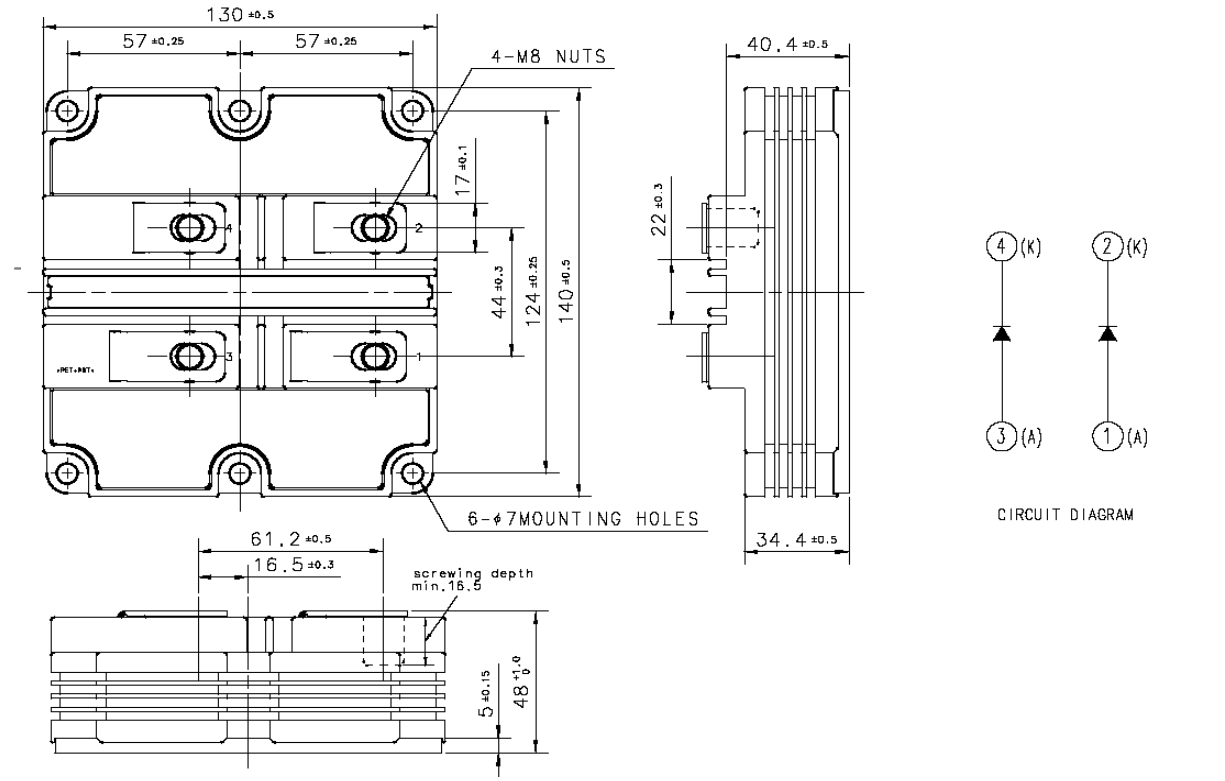
- I_F 250 A
- V_{RRM} 6500 V
- 2-element in a Pack
- High Insulated Type
- Soft Recovery Diode
- AISiC Baseplate

APPLICATION

Traction drives, High Reliability Converters / Inverters, DC choppers

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



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MAXIMUM RATINGS

Symbol	Item	Conditions	Ratings	Unit
V _{RRM}	Repetitive peak reverse voltage	T _J = +125°C	6500	V
		T _J = +25°C	6300	
		T _J = -50°C	5700	
V _{RSM}	Non-repetitive peak reverse voltage	T _J = +125°C	6500	V
		T _J = +25°C	6300	
		T _J = -50°C	5700	
I _F	Collector current	DC, T _C = 25°C	250	A
I _{FRM}		Pulse ^(Note 1)	500	A
I _{FSM}	Surge (non-repetitive) forward current	T _J = 125°C, V _R = 0 V, t = 10 ms	2350	A
I ² t	Surge forward current integral	T _J = 125°C, V _R = 0 V, t = 10 ms	28	kA ² s
V _{iso}	Isolation voltage	RMS, sinusoidal, f = 60Hz, t = 1 min.	10200	V
V _e	Partial discharge extinction voltage	RMS, sinusoidal, f = 60Hz, Q _{PD} ≤ 10 pC	5100	V
T _J	Junction temperature		-50 ~ +150	°C
T _{jop}	Operating temperature		-50 ~ +125	°C
T _{stg}	Storage temperature		-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit	
			Min	Typ	Max		
I _{RRM}	Repetitive reverse current	V _{RM} = V _{RRM}	T _J = 25°C	—	—	2.0	mA
			T _J = 125°C	—	2.0	10.0	
V _{FM}	Forward voltage	I _F = 250 A ^(Note 2)	T _J = 25°C	—	3.30	—	V
			T _J = 125°C	—	3.40	4.30	
t _{rr}	Reverse recovery time	V _{CC} = 3600 V I _C = 250 A V _{GE} = ±15 V L _s = 150 nH	T _J = 25°C	—	0.55	—	μs
			T _J = 125°C	—	0.60	—	
I _{rr}	Reverse recovery current	V _{CC} = 3600 V I _C = 250 A V _{GE} = ±15 V L _s = 150 nH	T _J = 25°C	—	260	—	A
			T _J = 125°C	—	290	—	
Q _{rr}	Reverse recovery charge	-d _{IF} /d _t = 1250 A/μs @ T _J = 25°C 1100 A/μs @ T _J = 125°C	T _J = 25°C	—	240	—	μC
			T _J = 125°C	—	340	—	
E _{rec(10%)}	Reverse recovery energy ^(Note 3)	Inductive load	T _J = 25°C	—	0.30	—	J/P
			T _J = 125°C	—	0.60	—	
E _{rec}	Reverse recovery energy ^(Note 4)	Inductive load	T _J = 25°C	—	0.40	—	J/P
			T _J = 125°C	—	0.80	—	

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THERMAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min	Typ	Max	
$R_{th(j-c)D}$	Thermal resistance	Junction to Case, 1/2 module	—	—	67.5	K/kW
$R_{th(c-f)}$	Contact thermal resistance	Case to Fin, $\lambda_{grease} = 1W/m \cdot K$ $D_{(c-s)} = 100 \mu m$, 1/2 module	—	48.0	—	K/kW

MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min	Typ	Max	
M_t	Mounting torque	M8: Main terminals screw	7.0	—	22.0	N·m
M_s		M6: Mounting screw	3.0	—	6.0	N·m
m	Mass		—	1.1	—	kg
CTI	Comparative tracking index		600	—	—	—
d_a	Clearance		26.0	—	—	Mm
d_s	Creepage distance		56.0	—	—	Mm
$L_{P AK}$	Parasitic stray inductance	1/2 module	—	44.0	—	nH
R_{AA+KK}	Internal lead resistance	$T_c = 25^\circ C$, 1/2 module	—	0.27	—	m Ω

- Note 1. Pulse width and repetition rate should be such that junction temperature (T_j) does not exceed T_{opmax} rating (125°C).
 Note 2. Pulse width and repetition rate should be such as to cause negligible temperature rise.
 Note 3. $E_{rec(10\%)}$ is the integral of $0.1V_R \times 0.1I_F \times dt$.
 Note 4. The integration range of E_{rec} according to IEC 60747.

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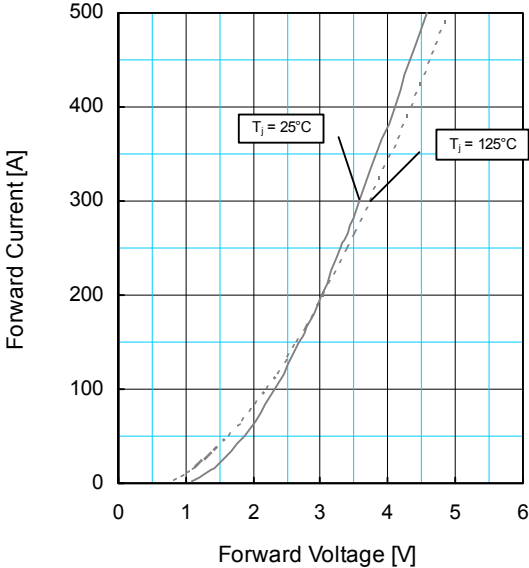
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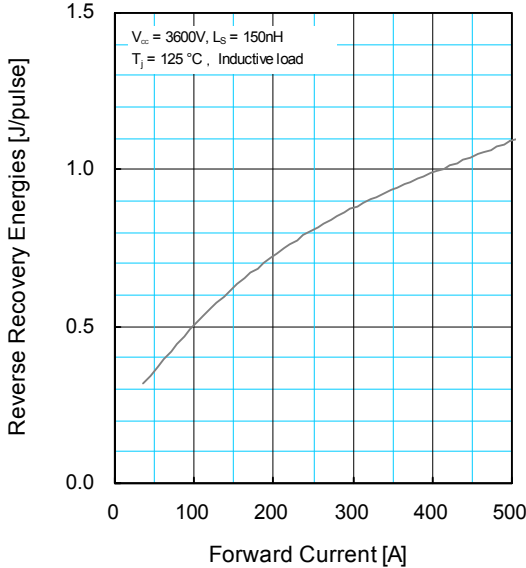
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PERFORMANCE CURVES

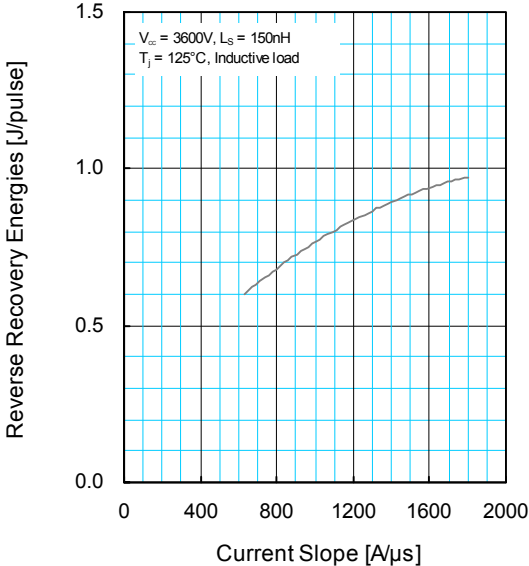
FORWARD CHARACTERISTICS (TYPICAL)



REVERSE RECOVERY CHARACTERISTICS (TYPICAL)



REVERSE RECOVERY CHARACTERISTICS (TYPICAL)



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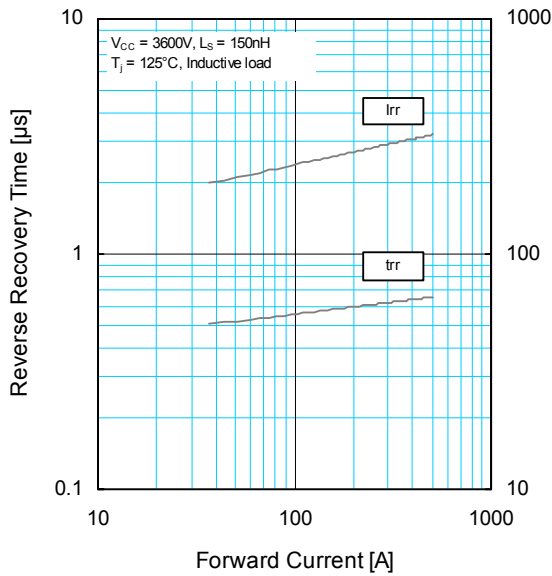
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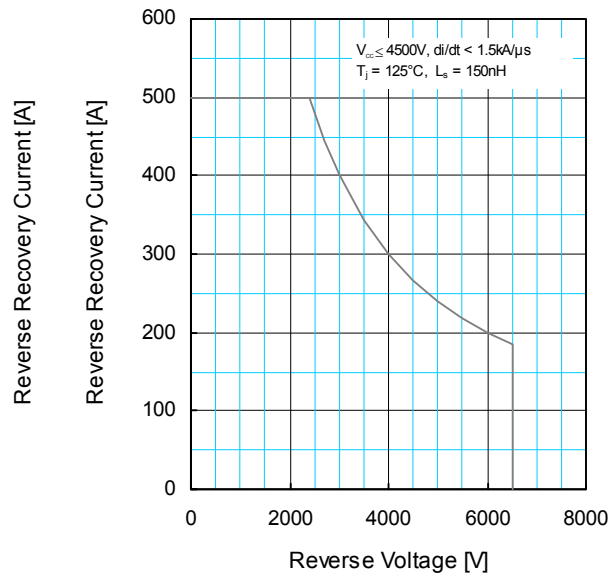
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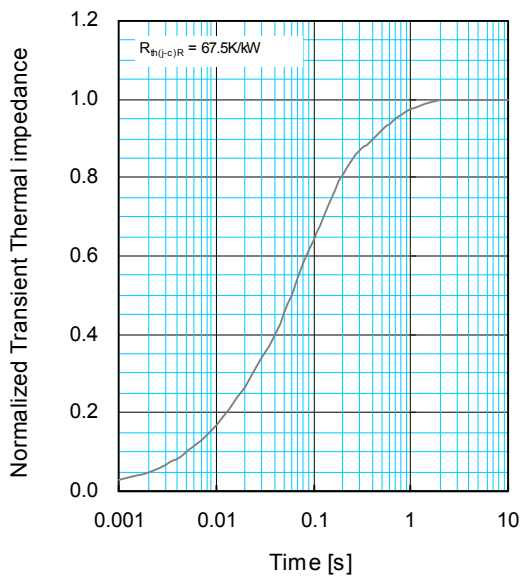
REVERSE RECOVERY CHARACTERISTICS (TYPICAL)



REVERSE RECOVERY SAFE OPERATING AREA (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS



$$Z_{th(j-c)}(t) = \sum_{i=1}^n R_i \left\{ 1 - \exp\left(-\frac{t}{\tau_i}\right) \right\}$$

	1	2	3	4
R_i [K/KW] :	0.0059	0.0978	0.6571	0.2392
τ_i [sec] :	0.0002	0.0074	0.0732	0.4488

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